

PATENT
1630-0135P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: SHIN, Johngeon Conf.:
Appl. No.: NEW Group:
Filed: January 28, 2004 Examiner:
For: CRYSTAL GROWTH METHOD OF NITRIDE
SEMICONDUCTOR

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

January 28, 2004

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

This amendment includes Amendments to the Specification and Remarks.